

Features

- 6 Amps Continuous Load Current
- Precision Internal 1% Reference
- 1.0V to 3.8V Output Voltage
- Internal Power MOSFETs
- >90% Efficiency
- Synchronous Switching
- Adjustable Slope Compensation
- Over Temperature Indicator
- Pulse by Pulse Current Limiting
- Operates up to 1MHz
- 1.5% Typical Output Accuracy
- Adjustable Oscillator w/Sync
- Remote Enable/Disable
- Intel P54 and P55 Compatible
- VCC2DET Interface
- Internal Soft Start

Applications

- PC Motherboards
- Local High Power CPU Supplies
- 5V to 1.0V DC-DC Conversion
- Portable Electronics/Instruments
- P54 and P55 Regulators
- GTL+ Bus Power Supply

Ordering Information

Part No.	Temp. Range	Package	Outline #
EL7556CM	0^{9} C to 70^{9} C	28-Pin SOIC	MDP0027

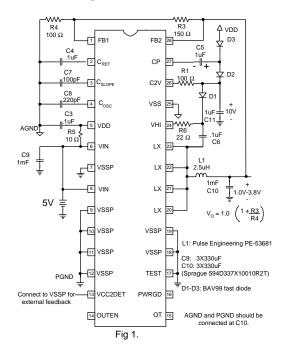
General Description

The EL7556C is an adjustable synchronous DC:DC switching regulator optimized for a 5V input and 1.0-3.8V output. By combining integrated NMOS power FETS with fused-lead packaging the EL7556 can supply up to 6A continuous output current without the use of external power devices or discrete heat sinks, thereby minimizing design effort and overall system cost.

On chip resistorless current sensing is used to achieve stable, highly efficient, current-mode control. The EL7556 also incorporates the VCC2DET function to directly interface with the Intel P54 and P55 microprocessors. Depending on the state of VCC2DET the output voltage is internally preset to 3.50V or a user-adjustable voltage using two external resistors. In both internal and external feedback modes the active-high PWRGD output indicates when the regulator output is within +/-10% of the programmed voltage. An on-board sensor monitors die temperature (OT) for over-temperature conditions and can be connected directly to OUTEN to provide automatic thermal shutdown. Adjustable oscillator frequency and slope compensation allow added flexibility in overall system design.



Connection Diagram



Absolute Maximum Ratings $(T_A = 25^{\circ}C)$

	0		
Storage Temperature Range	-65°C to +150°C	Operating Junction Temperature	135°C
Supply (V _{IN})	5.5V	Peak Output Current	9A
Ambient Operating Temperature	$0^{\circ}C$ to $+70^{\circ}C$	Power Dissipation	2.5W
Output Pins	-0.3V below GND, +0.3V above V _{DD}		

Important Note:

All parameters having Min/Max specifications are guaranteed. The Test Level column indicates the specific device testing actually performed during production and Quality inspection. Elantec performs most electrical tests using modern high-speed automatic test equipment, specifically the LTX77 Series system. Unless otherwise noted, all tests are pulsed tests, therefore $T_J=T_C=T_A$.

Test Level	Test Procedure
I	100% production tested and QA sample tested per QA test plan QCX0002.
II	100% production tested at $T_A = 25^{\circ}C$ and QA sample tested at $T_A = 25^{\circ}C$,
	TMAX and TMIN per QA test plan QCX0002.
III	QA sample tested per QA test plan QCX0002.
IV	Parameter is guaranteed (but not tested) by Design and Characterization Data.
V	Parameter is typical value at $T_{\!\rm A}=25^{\circ}{\rm C}$ for information purposes only.

DC Electrical Characteristics

Parameter	Description	Condition	Min	Тур	Max	Test Level	Units
V _{C2V}	Voltage doubler output	Vdd=5V, ILOAD=10mA	7.2	7.8	8.4	Ι	V
V _{REF}	Reference accuracy	IREF=0	1.157	1.169	1.181	Ι	V
V _{REFTC}	Reference voltage tempco			50		V	ppm
V _{REFLOAD}	Reference load regulation	0 <iload<1ma< td=""><td>5</td><td></td><td>.5</td><td>Ι</td><td>%</td></iload<1ma<>	5		.5	Ι	%
F _{RAMP}	Oscillator ramp amplitude			1.2		V	V
IOSC CHG	Oscillator charge current	.2V <vosc<1.4v< td=""><td></td><td>150</td><td></td><td>V</td><td>uA</td></vosc<1.4v<>		150		V	uA
I _{OSC DIS}	Oscillator discharge current	.2V <vosc<1.4v< td=""><td></td><td>5</td><td></td><td>V</td><td>mA</td></vosc<1.4v<>		5		V	mA
I _{PUP}	VCC2DET, OUTEN pull up current	VCC2DET, OUTEN=0	10	14	18	I	uA
I _{CSLOPE}	Cslope charging current		23	28.5	34	Ι	uA
I _{FR1}	FB1 input pull up current			2		V	uA
I _{DD}	V _{DD} supply current	OUTEN=4V, Fosc=120kHz		11	25	Ι	mA
IDDOFF	V _{DD} standby current	OUTEN=0		1.5	5	Ι	mA
I _{VIN}	V _{IN} no-load current	OUTEN=0		100	200	Ι	uA
ILEAK	LX output leakage to VSS	LX=0V			100	Ι	uA
R _{DSON}	Composite FET resistance		18		30	Ι	mohms
R _{DSONTC}	R _{DSON} tempco			.1		V	mΩ/C
V _{OUT1}	Output initial accuracy	VCC2DET=4V, IL=3A (See Fig. 1)	3.450	3.500	3.550	IV	V
V _{OUT2}	Output initial accuracy	VCC2DET=0V, IL=3A R3=150 Ω , R4=100 Ω (See Fig 1).	2.450	2.500	2.550	IV	V

 $V_{DD}=V_{IN}=5V, C_{osc}=1nF, C_{slope}=470pF, T_{A}=25C$ unless otherwise specified

DC Electrical Characteristics

Parameter	Description Condition Min Typ		Тур	Max	Test Level	Units	
V _{OUTLINE}	Output line regulation	VDD=5V, +/- 10%	-1		1	Ι	%
V _{OUTLOAD}	Output load regulation	.5A <i<sub>LOAD<6A, relative to IL=3A. Continuous mode of operation. (Fig 1)</i<sub>	-1		1	IV	%
I _{LMIN}	Minimum load current	OUTEN=4V		50		V	mA
R _{SHORT}	Short circuit load resistance. See Note 1.	IL=6A prior to continuous application of _{RSHORT} .OUTEN connected to OT.		100		V	mΩ
ILMAX	Current limit			9		V	А
V _{OUTTC}	Output tempco	$0 {}^{\rm o}{\rm C} < {\rm Ta} < 70 {}^{\rm o}{\rm C}$		+/-1		V	%
T _{OT}	Over temperature threshold			120		V	°C
T _{HYS}	Over temperature hysteresis			40		V	°C
R _{OT}	Over temperature pull up resistance	OT=0V	12	20	28	Ι	kΩ
V _{PWGD}	Power good threshold relative to programmed output voltage	VCC2SEL=4V, VOUT=3.50V	<u>+</u> 6	<u>+</u> 10	<u>+</u> 14	Ι	%
V _{DDOFF}	Maximum VDD for shutdown		3.15			Ι	v
V _{DDON}	Minimum VDD for startup				4.15	Ι	v
V _{HYS}	Supply input hysterisis	V _{HYS} =V _{DDON} -V _{DDOFF}		.5		V	v
V _{IH}	VCC2DET, OUTEN input high .		4			Ι	v
V _{II.}	VCC2DET, OUTEN input low.				.8	Ι	V
V _{OH_PWGD}	Powergood drive high	Iload=1mA	3.5			Ι	V
V _{OL_PWDG}	Powergood drive low	Iload=-1mA			1.0	Ι	V

 $V_{pp}=V_{pq}=5V$, $C_{ace}=1nF$, $C_{close}=470pF$, $T_{A}=25C$ unless otherwise specified

Note 1: When operating at maximum load current a short circuit from Vout to GND of less than 100m Ω may cause the IC to enter a nondestructive latch up mode. If latchup occurs the power supply to the IC must be recycled to resume normal operation. To protect the IC under short circuit conditions connect OUTEN to OT. Prolonged operation a latched state is not recommended.

AC Electrical Characteristics

 $V_{DD}=V_{IN}=5V$, $C_{osc}=1nF$, $C_{slope}=470pF$, $T_{A}=25C$ unless otherwise specified

Parameter	Description	Condition	Min	Тур	Max	Test Level	Units
F _{OSC}	Oscillator initial accuracy		100	120	140	Ι	kHz
t	Minimum oscillator sync width 50			v	ns		
M _{SS}	Soft start slope (See Fig 1).			7		v	V/msec
t _{brm}	FET break before make delay 10			ns			
t _{LEB}	High side FET minimum on time (LEB)			100		v	ns
D _{MAX}	Maximum duty cycle			96		V	%

Pin Number	Name	Pin Type	Description
1	FB1	I	Voltage feedback for the buck regulator. Active when VCC2DET is logic low. Normally connected to external resistor divider between VOUT and GND. A 2uA pull-up current forces VOUT to VSS in the event that FB1 is floating and VCC2DET is inadvertently connected to GND.
2	CREF	I	Bandgap reference bypass capacitor. Typically .47uF to VSS.
3	CSLOPE	Ι	Slope compensation capacitor. Ramp width corresponds to LX duty cycle. C_{SLOPE} to C_{OSC} ratio is normally 1:2.2
4	COSC	Ι	Oscillator timing capacitor. Fosc(Hz) can be approximated by: Fosc(kHz)=.0001/C _{OSC} . C _{OSC} in Farads
5	VDD	S	Power Supply for PWM control circuitry. Normally the same potential as VIN.
6	VIN	S	Power Supply input to the buck regulator. Connected to the drain of the high-side NMOS FET.
7	VSSP	S	Ground return to the buck regulator. Connected to the source of the low-side synchronous NMOS FET.
8	VIN	S	Same as pin 6.
9	VSSP	S	Same as pin 7.
10	VSSP	S	Same as pin 7.
11	VSSP	S	Same as pin 7.
12	VSSP	S	Same as pin 7.
13	VCC2DET	I	VCC2DET interface logic input. When driven to logic 1 V_{OUT} =3.500V, When driven to logic 0 the PWM uses FB1 to determine V_{OUT} : VOUT=1.0V*(1+R3/R4).
14	OUTEN	Ι	The switching regulator output is enabled when logic 1. The reference voltage output operates whenever the power supply is qualified (VDD > VPOR) regardless of the state of this pin.
15	ОТ	0	Over temperature indicator. Normally high. Pulls low when die temperature exceeds 120C, returns to the hig state when die temperature has cooled to 80C.
16	PWRGD	0	Power good window comparator output. Logic 1 when regulator output is within +/-10% of programmed voltage.
17	TEST	Ι	Test pin. Must be connected to VSSP in normal operation.
18	VSSP	S	Same as pin 7.
19	VSSP	S	Same as pin 7.
20	LX	0	Inductor drive pin. High current digital output whose average voltage equals the regulator output voltage.
21	LX	0	Same as pin 20.
22	LX	0	Same as pin 20.
23	LX	0	Same as pin 20.
24	VHI	I	Gate drive to high side driver. Bootstrapped from LX with a .1uF capacitor.
25	VSS	S	Ground return for internal control circuitry.
26	C2V	I	Connected to voltage doubler output. Supplies gate drive to the low-side driver.
27	СР	0	Drives the negative side of charge pump capacitor at one-half the oscillator frequency Fosc.
28	FB2	I	Voltage feedback pin. Active when VCC2DET is logic 1. Internally preset to V _{OUT} =3.50V

EL7556C Pin Description (I=Input O=Output S=Supply)

Circuit Description

General

The EL7556 is a fixed frequency, current mode controlled DC:DC converter with integrated Nchannel power MOSFETS and a high precision reference. The device incorporates all of the active circuitry required to implement a cost effective, userprogrammable 6A synchronous buck converter suitable for use in CPU power supplies. By combining fused-lead packaging technology with the efficient synchronous switching architecture high power outputs (21W) can be realized without the use of discrete external heat sinks.

Theory of Operation

The EL7556 is composed of 6 major blocks:

- PWM Controller
- Output Voltage Mode Select
- NMOS Power FETS and Drive Circuitry
- Bandgap Reference
- Oscillator
- Temperature Sensor
- Power Good and Power On Reset

PWM Controller

The EL7556 regulates output voltage through the use of current-mode controlled pulse width modulation. The three main elements in a PWM controller are the feedback loop and reference, a pulse width modulator whose duty cycle is controlled by the feedback error signal, and a filter which averages the logic level modulator output. In a step-down (buck) converter, the feedback loop forces the timeaveraged output of the modulator to equal the desired output voltage. Unlike pure voltage-mode control systems current-mode control utilizes dual feedback loops to provide both output voltage and inductor current information to the controller. The voltage loop minimizes DC and transient errors in the output voltage by adjusting the PWM duty-cycle in response to changes in line or load conditions. Since the output voltage is equal to the time-average of the modulator output the relatively large LC time constants found in power supply applications generally results in low bandwidth and poor transient response. By directly monitoring changes in inductor current via a series sense resistor the controller's response time is not entirely limited by the output LC filter and can react more quickly to changes in line or load conditions. This feed-forward characteristic also simplifies AC loop compensation since it adds a zero to the overall loop response. Through proper selection of the current-feedback to voltage-feedback ratio the overall loop response will approach a one pole system. The resulting system offers several advantages over traditional voltage control systems, including simpler loop compensation, pulse by pulse current limiting, rapid response to line variation and good load step response.

The heart of the controller is a triple-input direct summing comparator which sums voltage feedback, current feedback and slope compensating ramp signals together. Slope compensation is required to prevent system instability which occurs in currentmode topologies operating at duty-cycles greater than 50% and is also used to define the open-loop gain of the overall system. The compensation ramp amplitude is user adjustable and is set using a single external capacitor (CSLOPE). Each comparator input is weighted and determines the load and line regulation characteristics of the system. Current feedback is measured by sensing the inductor current flowing through the high-side switch whenever it is conducting. At the beginning of each oscillator period the high-side NMOS switch is turned on and CSLOPE ramps positively from it's reset state (VREF potential). The comparator inputs are gated off for a minimum period of time (LEB) after the high-side switch is turned on to allow the system to settle. The Leading Edge Blanking (LEB) period prevents the detection of erroneous voltages at the comparator inputs due to switching noise. When programming low regulator output voltages the LEB delay will limit the maximum operating frequency of the circuit since the LEB will result in a minimum duty-cycle regardless of the PWM error voltage. This relationship is shown in the performance curves. If the inductor current exceeds the maximum current limit (ILMAX) a secondary over-current comparator will terminate the high-side switch on time. If ILMAX has not been reached the regulator output voltage is then compared to the reference voltage VREF. The resultant error voltage is then summed with the current feedback and slope compensation

ramp. The high-side switch remains on until all three comparator inputs have summed to zero at which time the high-side switch is turned off and the low-side switch is turned on. In order to eliminate cross-conduction of the high-side and low-side switches a 10ns break-before-make delay is incorporated in the switch driver circuitry. In the continuous mode of operation the low-side switch will remain on until the end of the oscillator period. In order to improve the low current efficiency of the EL7556 a zero-crossing comparator senses when the inductor transitions through zero. Turning off the low-side switch at zero inductor current prevents forward conduction through the internal clamping diodes (LX to VSSP) when the low-side switch turns off and reduces power dissipation. The output enable (OUTEN) input allows the regulator output to be disabled by an external logic control signal.

Output Voltage Mode Select

The VCC2DET multiplexes the FB1 and FB2 pins to the PWM controller. A logic 1 on VCC2DET selects the FB2 input and forces the output voltage to the internally programmed value of 3.50V. A logic zero on VCC2DET selects FB1 and allows the output to be programmed from 1.0 to 3.8V. In general:

Vout=1.0V (1+R3/R4) Volt.

However, due to the relatively low open loop gain of the system, gain errors will occur as the output voltage and loop-gain are changed. This is shown in the performance curves. (The output voltage is factory trimmed to minimize error at a 2.50V output). A 2uA pull-up current from FB1 to VIN forces Vout to GND in the event that FB1 is not used and the VCC2DET is inadvertently toggled between the internal and external feedback mode of operation.

NMOS Power FETS and Drive Circuitry

The EL7556 integrates low resistance $(25m\Omega)$ NMOS FETS to achieve high efficiency at 6A. Gate drive for both the high-side and low-side switches is derived through a charge pump consisting of the CP pin and external components D1-D3 and C5-C6. The CP output is a low resistance inverter driven at onehalf the oscillator frequency. This is used in conjunction with D2-D3 to generate a 7.8V (typical) voltage on the C2V pin which provides gate drive to the low-side NMOS switch and associated level shifter. In order to use an NMOS switch for the highside drive it is necessary to drive the gate voltage above the source voltage (LX). This is accomplished by boot-strapping the VHI pin above the C2V voltage with capacitor C6 and diode D1. When the low-side switch is turned on the LX voltage is close to GND potential and capacitor C6 is charged through diodes D1-D3 to approximately 7.2V. At the beginning of the next cycle the high side switch turns on and the LX pin begins to rise from GND to VDD potential. As the LX pin rises the positive plate of capacitor C6 follows and eventually reaches a value of approximately 11.5V, for VDD=5V. This voltage is then level shifted and used to drive the gate of the high-side FET via the VHI pin.

Reference

A 1% temperature compensated band gap reference is integrated in the EL7556. The external C_{REF} capacitor acts as the dominant pole of the amplifier and can be increased in size to maximize transient noise rejection. A value of .47uF is recommended.

Oscillator

The system clock is generated by an internal relaxation oscillator with a maximum duty-cycle of approximately 96%. Operating frequency can be adjusted through the (COSC) pin or can be driven by an external clock source. If the oscillator is driven by an external source care must be taken in the selection of CSLOPE. Since the COSC and CSLOPE values determine the open loop gain of the system, changes to COSC require corresponding changes to CSLOPE in order to maintain a constant gain ratio. The recommended ratio of COSC to CSLOPE is 2.2:1

Temperature Sensor

An internal diode-based temperature sensor continuously monitors die temperature. In the event that the temperature exceeds the thermal trip-point the OT pin will output a logic 0. The upper and lower trip points are set to 120 °C and 80 °C respectively. To enable thermal shutdown this pin should be tied directly to OUTEN. Use of this feature is recommended during normal operation

Note: When operating at the maximum load current

a short circuit from Vout to GND of less than $100m\Omega$ may cause the part to enter a nondestructive latch-up mode. If latchup does occur the power supply to the IC must be recycled. In order to protect the IC under these conditions connect OT to OUTEN.

Power Good and Power On Reset

During power up the output regulator will be disabled until the VIN power supply reaches a value of approximately 4.0V. Approximately 300mV of hysterisis is present to eliminate noise induced oscillations.

Under-voltage and over-voltage conditions on the regulator output are detected through an internal window comparator. A logic 1 on the PWRGD output indicates that the regulated output voltage is within +/- 10% of the nominally programmed output voltage. Although small, the typical values of the PWRGD threshold will also vary with changes to external feedback (and resultant loop gain) of the system. This dependence is shown in the typical performance curves.

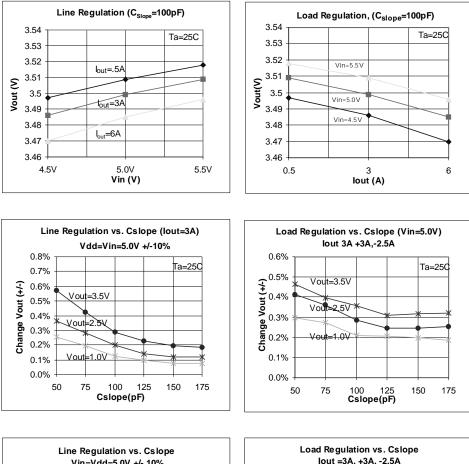
Thermal Management

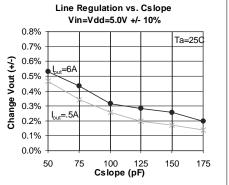
The EL7556 utilizes fused-lead packaging technology in conjunction with the system board layout to achieve a lower thermal resistance than typically found in standard 28 Lead SOIC packages. By fusing multiple leads to the die substrate thermal

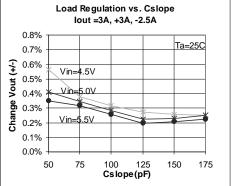
energy flows through a thermally conductive path (metal) instead of thermally resistive plastic. After conducting heat from the die to the leads heat transfer occurs by convection. If a sufficient amount of metal area is connected to the package leads a junction -to- ambient resistance of 31 °C/W can be achieved compared to 100 °C/W found in standard packages. The general relationship between board area and thermal resistance for this package is shown in the performance curves. It can be readily seen that the thermal resistance approaches an asymptotic value of approximately 31 °C/W. Additional information can be found in Application Note #8 (Measuring the Thermal Resistance of Power Surface-Mount Packages), and Application Note #13 (EL75XX Thermal Design Considerations).

If the thermal shutdown pin is connected to OUTEN the IC will enter thermal shutdown when the maximum junction temperature is reached. For a thermal shutdown of 120 °C and power dissipation of 2.2W the ambient temperature is limited to a maximum value of 50 °C (typical). The ambient temperature range can be extended with the application of airflow. For example, the addition of 100LFM reduces the thermal resistance by approximately 15% and can extend the operating ambient to 60 °C (typical). Since the thermal performance of the IC is heavily dependent on the board layout the system designer should exercise care during the design phase to ensure that the IC will operate under the worst-case environmental conditions.

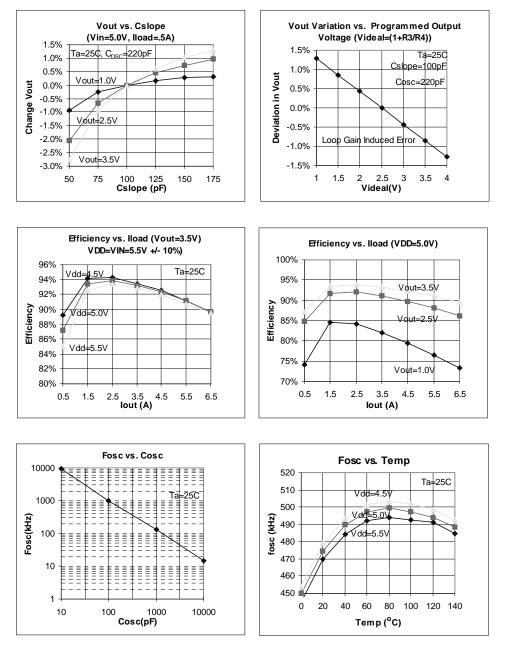
Typical Performance Curves





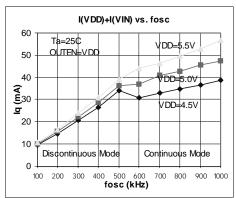


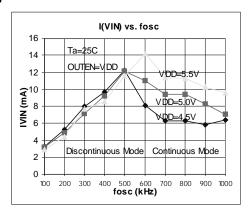
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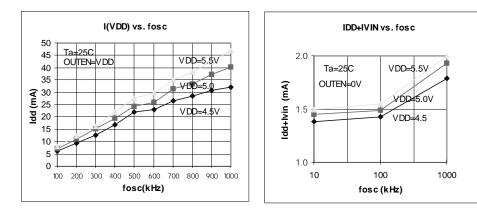


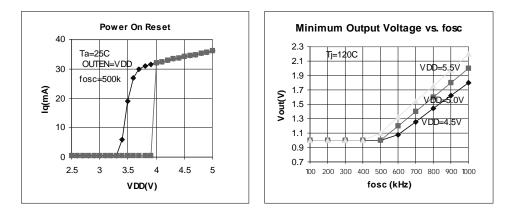
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Typical Performance Curves

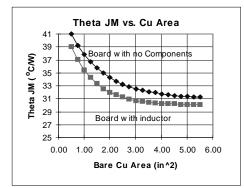


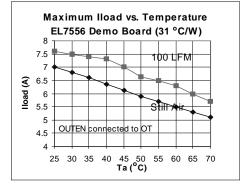


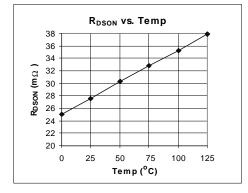




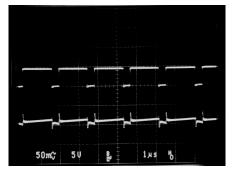
Typical PerformanceCurves



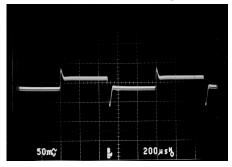




Top Trace: V(LX) Bottom Trace: VOUT, ILOAD=6A



VOUT, IL= .5A to 6A Load Step



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Block Diagram

